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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/981,842	10/19/2001	Kenji Imanishi	011287	7067
23850 7	590 10/01/2002			
ARMSTRONG,WESTERMAN & HATTORI, LLP 1725 K STREET, NW. SUITE 1000			EXAMINER	
			BAUMEISTER, BRADLEY W	
WASHINGTON, DC 20006			ART UNIT	PAPER NUMBER
			2815	
			DATE MAILED: 10/01/2002	

Please find below and/or attached an Office communication concerning this application or proceeding.

# Office Action Summary

Application No. 09/981,842

Applicant(s)

lmanishi

Examiner

**B.** William Baumeister

Art Unit 2815

The MAILING DATE of this communication appears on the cover sheet with the correspondence address						
Period for Reply A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.						
- Extens mailing	sions of time may be available under the provisions of 37 CFR 1.136 (a). In g date of this communication.  period for reply specified above is less than thirty (30) days, a reply within the					
- If NO p - Failure - Any re	period for reply is specified above is less than thirty (30) days, a reply within to beeriod for reply is specified above, the maximum statutory period will apply to reply within the set or extended period for reply will, by statute, cause to ply received by the Office later than three months after the mailing date of patent term adjustment. See 37 CFR 1.704(b).	r and will expire SIX (6) MONTHS from the mailin the application to become ABANDONED (35 U.S	ng date of this communication. S.C. § 133).			
Status						
1) 💢	Responsive to communication(s) filed on Jun 18, 2	2002	·			
2a) 🗌	This action is <b>FINAL</b> . 2b) X This ac	ction is non-final.				
3) 🗌	Since this application is in condition for allowance closed in accordance with the practice under $Ex\ partial$	except for formal matters, prosec arte Quayle, 1935 C.D. 11; 453	cution as to the merits is O.G. 213.			
·	tion of Claims					
4) 💢	Claim(s) 1-11	is/are	pending in the application.			
4	a) Of the above, claim(s) 4	is/ard	e withdrawn from consideration.			
	Claim(s)		is/are allowed.			
	0111110 1511		is/are rejected.			
7) 🗆	Claim(s)		is/are objected to.			
	Claims		tion and/or election requirement.			
Application Papers						
9) 🗆	The specification is objected to by the Examiner.					
10)	The drawing(s) filed on is/are	ea) □ accepted or b) □ objecte	d to by the Examiner.			
	Applicant may not request that any objection to the o					
11)	The proposed drawing correction filed on		b) $\square$ disapproved by the Examiner.			
_	If approved, corrected drawings are required in reply					
	The oath or declaration is objected to by the Exam	iner.				
	under 35 U.S.C. §§ 119 and 120	, , , , , , , , , , , , , , , , , , , ,				
	Acknowledgement is made of a claim for foreign p $All\ b)\Box$ Some* c) $\Box$ None of:	riority under 35 U.S.C. § 119(a)-	·(d) or (f).			
	I. $old \!$					
	B. Copies of the certified copies of the priority data application from the International Bure te the attached detailed Office action for a list of the	eau (PCT Rule 17.2(a)).	this National Stage			
_	Acknowledgement is made of a claim for domestic		a).			
	a) The translation of the foreign language provisional application has been received.					
15) ☐ Acknowledgement is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
Attachme	ent(s)	_				
_	ice of References Cited (PTO-892)	4) Interview Summary (PTO-413) Paper N				
	ice of Draftsperson's Patent Drawing Review (PTO-948)	5) Notice of Informal Patent Application (P	PTO-152)			
3) [ <b>X</b> ] imo	rmation Disclosure Statement(s) (PTO-1449) Paper No(s)4	6) Other:				

#### **DETAILED ACTION**

## Election/Restriction

- 1. Applicant's election without traverse of invention I in Paper No. 6 is acknowledged.
- 2. Upon further consideration, the Examiner is of the opinion that an examination of non-elected Species II in addition to elected species I would not constitute an undue burden.

  Accordingly, claim 8 has been rejoined. Claim 4, directed towards species III, remains withdrawn from consideration.

## Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 4. Claims 1-3, 5-8, 10 and 11 are rejected under 35 U.S.C. 102(b) as being anticipated by Higuchi et al. JP '934. Higuchi discloses a HEMT including an InP substrate 1; a buffer 2; an undoped 20-nm AlGaInAs stress-reducing (or second channel) layer 3; an InGaAs (first) channel 4; and an InAlAs electron supply layer 5-7 including a doped region 6. The aluminum concentration of the AlGaInAs layer 3 is disclosed as being about 0.4 (e.g., Fig 1).

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a. While Higuchi refers to the AlGaInAs layer as a stress-reducing layer as opposed to a second channel layer, the label is immaterial because the device layers have the same thicknesses and compositions disclosed and claimed. Accordingly, the stress-reducing layer inherently also functions as a second channel layer.

5. Claims 1, 2 and 8 are rejected under 35 U.S.C. 102(b) as being anticipated by Kohara et al. '542. Kohara teaches HEMTs formed on InP substrates that include a buffer; an undoped second channel 23a composed of In.8Ga.2As; an undoped first channel 23b composed of In.53Ga.47As and an electron supply layer that includes doped regions such as the (In/Al)As superlattice 25 (FIG 4) or the n-InAlAs layer 81 (FIG 15).

### Claim Rejections - 35 USC § 103

- 6. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 7. Claim 9 is rejected under 35 U.S.C. 103(a) as being unpatentable over Higuchi as applied to the claims above, and further in view of Applicant's Prior Art admissions. Regardless of whether Higuchi '934 teaches that the HEMT thereof may be etched to the buffer, Applicant

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acknowledges that it was known to etch HEMTs to the buffer layer (see e.g., BACKGROUND). It would have been obvious to one of ordinary skill in the art at the time of the invention to have etched the HEMT of Higuchi '934 down to the buffer for the purpose of providing carrier isolation between the HEMT and any other devices integrated on the InP substrate.

#### Conclusion

- 8. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
- a. Imamura '356 teaches memory devices and HEMTs integrated on InP substrates that have undoped InAlGaAs layers interposed between the buffer and the InGaAs channel. (See e.g., FIGs 7 and 10A,C.)

#### INFORMATION ON HOW TO CONTACT THE USPTO

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to the examiner, **B. William Baumeister**, at (703) 306-9165. The examiner can normally be reached Monday through Friday, 8:30 a.m. to 5:00 p.m. If the Examiner is not available, the Examiner's supervisor, Mr. Eddie Lee, can be reached at (703) 308-1690. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956.

B. William Baumeister

Patent Examiner, Art Unit 2815

September 25, 2002